



# 30V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8 (Type UX)

#### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>C</sub> = +25°C
30V	5.5mΩ @ V <sub>GS</sub> = 10V	60A
	9.0mΩ @ V <sub>GS</sub> = 4.5V	50A

#### **Features and Benefits**

- Low R<sub>DS(ON)</sub>—Ensures On-State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- The DMN3009LFVQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

#### **Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

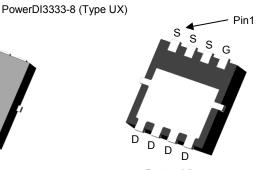
- Backlighting
- Power Management Functions
- DC-DC Converters

#### **Mechanical Data**

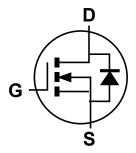
- Case: PowerDI<sup>®</sup>3333-8 (Type UX)
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Lead-Frame.
   Solderable per MIL-STD-202, Method 208 3
- Weight: 0.072 grams (Approximate)







**Bottom View** 



**Equivalent Circuit** 

#### **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMN3009LFVQ-7	PowerDI3333-8 (Type UX)	2000/Tape & Reel
DMN3009LFVQ-13	PowerDI3333-8 (Type UX)	3000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### **Marking Information**



SH1= Product Type Marking Code

YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 20 = 2020)
WW = Week Code (01 to 53)



### Maximum Ratings (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	$V_{DSS}$	30	V	
Gate-Source Voltage	$V_{GSS}$	±20	V	
Continuous Drain Current (Note 7) V <sub>GS</sub> = 10V	$T_C$ = +25°C $T_C$ = +70°C	ID	60 50	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	90	Α	
Maximum Continuous Body Diode Forward Current (Note 7)		Is	60	Α
Avalanche Current, L = 0.1mH (Note 8)		I <sub>AS</sub>	33	Α
Avalanche Energy, L = 0.1mH (Note 8)	E <sub>AS</sub>	58	mJ	

## Thermal Characteristics (@ $T_A$ = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Total Power Dissipation (Note 5)		$P_{D}$	1.0	W	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\Theta JA}$	126	°C/W	
Total Power Dissipation (Note 6)		$P_{D}$	2.0	W	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>OJA</sub>	62	°C/W	
Thermal Resistance, Junction to Case (Note 7)		Rejc	3.5	C/VV	
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C	

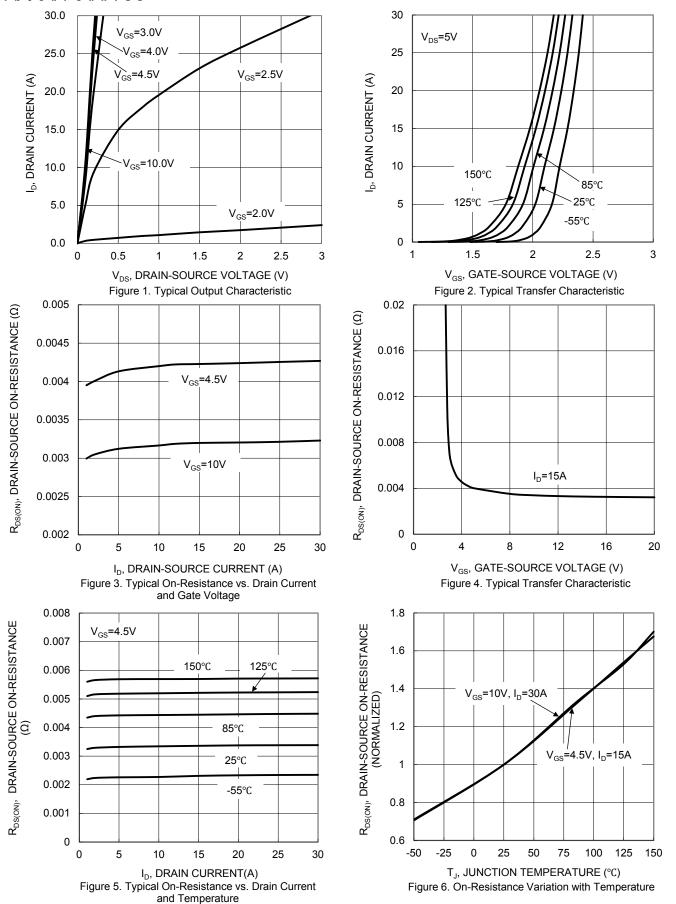
### Electrical Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 24V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	_	3	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		_	3.5	5.5	mΩ	$V_{GS} = 10V, I_D = 30A$	
Static Dialii-Source Off-Resistance	R <sub>DS(ON)</sub>	_	4.6	9.0		$V_{GS} = 4.5V, I_D = 15A$	
Diode Forward Voltage	$V_{SD}$	_	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C <sub>iss</sub>	_	2,000	_	pF	\\ -45\\\\ -0\\	
Output Capacitance	Coss		315	_	pF	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	-	247	_	pF	11 - 11VIFIZ	
Gate Resistance	$R_{g}$	_	2.2	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	20	_	nC		
Total Gate Charge (V <sub>GS</sub> = 10V)	$Q_g$	_	42	_	nC	\/ - 45\/   - 45A	
Gate-Source Charge	Qgs	_	4.7	_	nC	V <sub>DS</sub> = 15V, I <sub>D</sub> = 15A	
Gate-Drain Charge	$Q_{gd}$	_	7.4	_	nC		
Turn-On Delay Time	t <sub>D(ON)</sub>	_	3.9	_	ns		
Turn-On Rise Time	t <sub>R</sub>	_	4.1	_	ns	$V_{DD}$ = 15V, $V_{GS}$ = 10V, $R_{G}$ = 3.3 $\Omega$ , , $I_{D}$ = 15A	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	31	_	ns		
Turn-Off Fall Time	t <sub>F</sub>	_	15	_	ns		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	-	15	_	ns	1 - 15 \ di/dt - 100 \/ \/ \/ \c	
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	_	6.0	_	nC	$I_F = 15A$ , di/dt = 100A/ $\mu$ s	

Notes:

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
  7. Thermal resistance from junction to soldering point (on the exposed drain pad).
  8. I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  9. Short duration pulse test used to minimize self-heating effect.
  10. Guaranteed by design. Not subject to product testing.







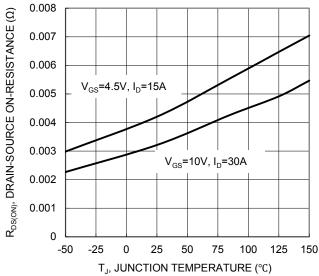


Figure 7. On-Resistance Variation with Temperature

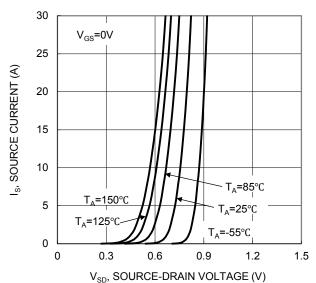


Figure 9. Diode Forward Voltage vs Current

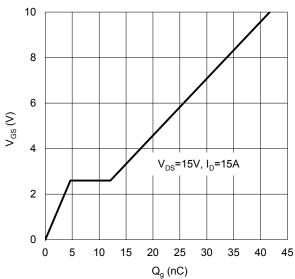


Figure 11. Gate Charge

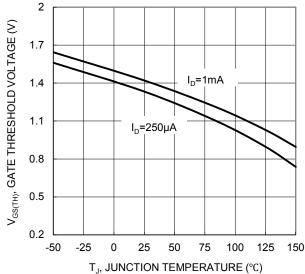


Figure 8. Gate Threshold Variation vs. Junction Temperature

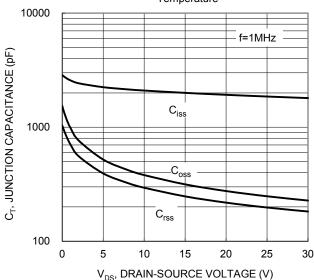


Figure 10. Typical Junction Capacitance

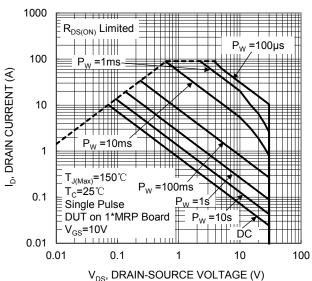


Figure 12. SOA, Safe Operation Area



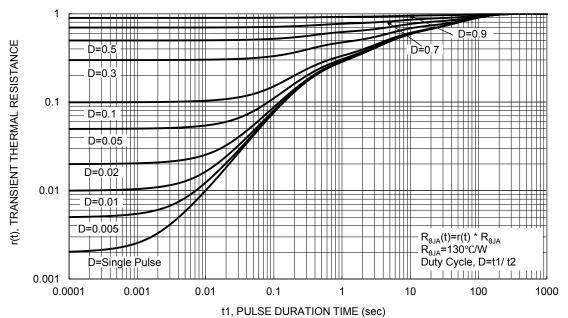
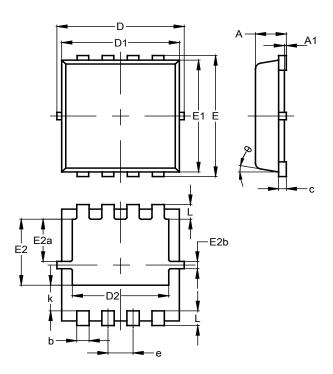


Figure 13. Transient Thermal Resistance



### **Package Outline Dimensions**

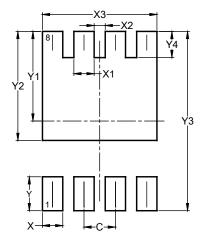
Please see http://www.diodes.com/package-outlines.html for the latest version.



PowerDI3333-8 (Type UX)					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05			
b	0.25	0.40	0.32		
С	0.10	0.25	0.15		
D	3.20	3.40	3.30		
D1	2.95	3.15	3.05		
D2	2.30	2.70	2.50		
Е	3.20	3.40	3.30		
E1	2.95	3.15	3.05		
E2	1.60	2.00	1.80		
E2a	0.95	1.35	1.15		
E2b	0.10	0.30	0.20		
е	0.65 BSC				
k	0.50	0.90	0.70		
L	0.30	0.50	0.40		
θ	0°	12°	10°		
All Dimensions in mm					

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)			
С	0.650			
X	0.420			
X1	0.420			
X2	0.230			
Х3	2.370			
Υ	0.700			
Y1	1.850			
Y2	2.250			
Y3	3.700			
Y4	0.540			



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